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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Fazan et al.
 Appl. No. : 09/037,945
 Filed : March 10, 1998
 For : STREAMLINED FIELD ISOLATION PROCESS
 Examiner : George Fourson

Group Art Unit 2823

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AMENDMENT AFTER FINAL

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Dear Sir:

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This is a response to the Office Action mailed on January 12, 2000, in which all of the pending claims were finally rejected. This Amendment After Final amends all of the pending claims, but is not believed to raise new issues. Rather, it is believed that the amendments clarify the claimed process in a manner which avoids the prior art without altering the principal focus of the claims. For this reason, and because the amendments clarify the patentable features of the method for any possible appeal, entry of these amendments is earnestly solicited.

In the Claims:

1. (Thrice Amended) A process of forming an integrated circuit, comprising:
 growing a silicon dioxide field isolation region on a semiconductor wafer
without forming silicon nitride inclusions in said field isolation region exclusively by means of a hydrogen-free oxidant at a pressure less than about 30 atm; and forming a gate oxide without a prior sacrificial oxidation.
8. (Thrice Amended) A field isolation region among integrated circuit devices on a semiconductor substrate formed by a process comprising: